

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, b}	Q_g (Typ.)
- 30	0.088 at $V_{GS} = - 10$ V	- 2.7	4.1 nC
	0.138 at $V_{GS} = - 4.5$ V	- 2.2	

FEATURES

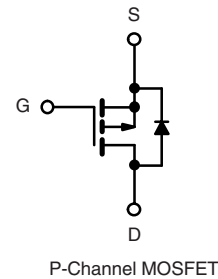
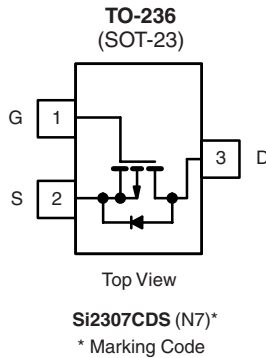
- Halogen-free Option Available
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT

APPLICATIONS

- Load Switch for Portable Devices



Ordering Information: Si2307CDS-T1-E3 (Lead (Pb)-free)
Si2307CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	$T_C = 25$ °C	- 3.5	A
	$T_C = 70$ °C	- 2.8	
	$T_A = 25$ °C	- 2.7 ^{a, b}	
	$T_A = 70$ °C	- 2.2 ^{a, b}	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	- 12	
Continuous Source-Drain Diode Current ^{a, b}	$T_C = 25$ °C	- 1.5	
	$T_A = 25$ °C	- 0.91 ^{a, b}	
Maximum Power Dissipation ^{a, b}	$T_C = 25$ °C	1.8	W
	$T_C = 70$ °C	1.14	
	$T_A = 25$ °C	1.1 ^{a, b}	
	$T_A = 70$ °C	0.7 ^{a, b}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^c		260	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	90	115	°C/W	
Maximum Junction-to-Foot (Drain)	R_{thJF}	55	70		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. $t = 5$ s.

c. Maximum under Steady State conditions is 166 °C/W.



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-32		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		4.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			-100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq 5\text{ V}, V_{GS} = -10\text{ V}$	-6			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.5\text{ A}$		0.073	0.088	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		0.110	0.138	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -3.5\text{ A}$		7		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		340		pF
Output Capacitance	C_{oss}		67			
Reverse Transfer Capacitance	C_{rss}		51			
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		4.1	6.2	nC
Gate-Source Charge	Q_{gs}		1.3			
Gate-Drain Charge	Q_{gd}		1.8			
Gate Resistance	R_g	$f = 1\text{ MHz}$		10		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		40	60	ns
Rise Time	t_r		40	60		
Turn-Off Delay Time	$t_{d(off)}$		20	40		
Fall Time	t_f		17	30		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		5.5	10	
Rise Time	t_r		13	25		
Turn-Off Delay Time	$t_{d(off)}$		17	30		
Fall Time	t_f		7.7	15		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-1.5	A
Pulse Diode Forward Current	I_{SM}				-12	
Body Diode Voltage	V_{SD}	$I_S = -0.75\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		17	30	ns
Body Diode Reverse Recovery Charge	Q_{rr}		11	20	nC	
Reverse Recovery Fall Time	t_a		12		ns	
Reverse Recovery Rise Time	t_b		5			

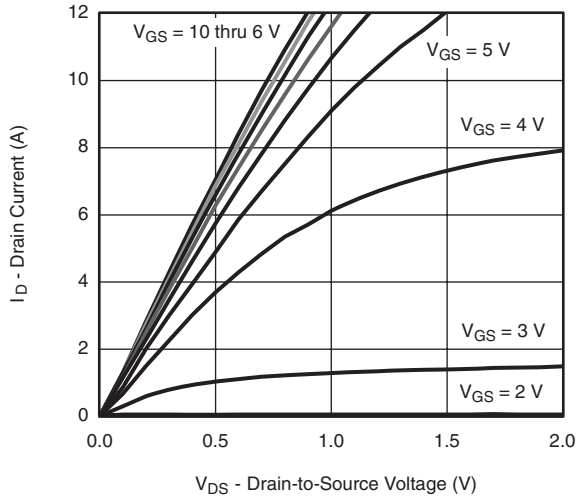
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

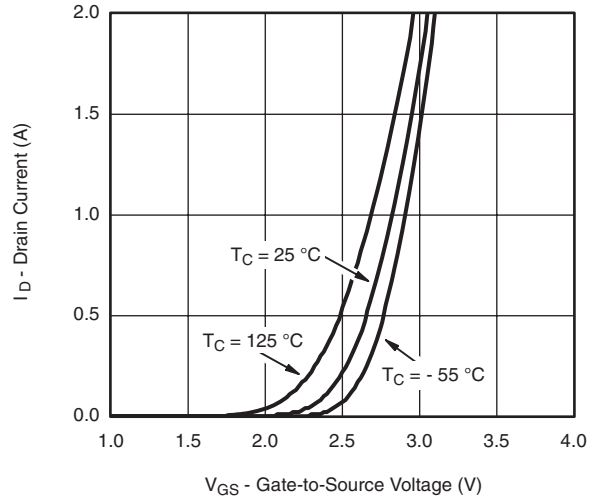
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



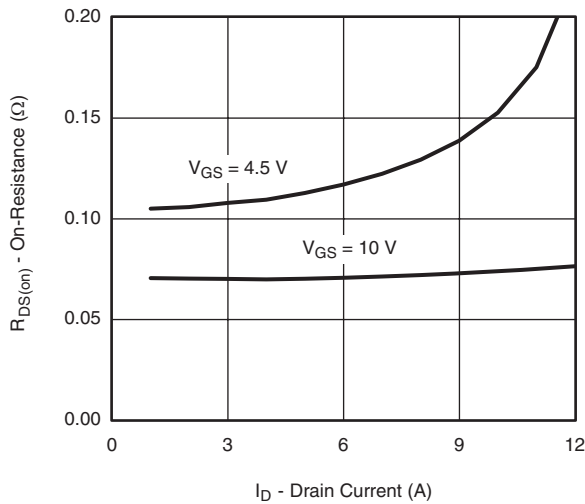
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



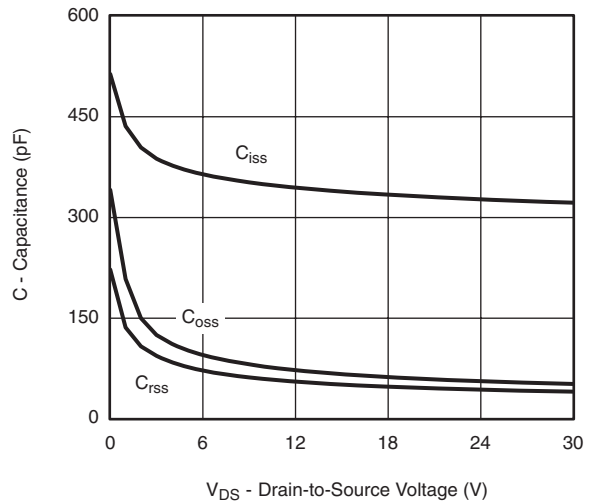
Output Characteristics



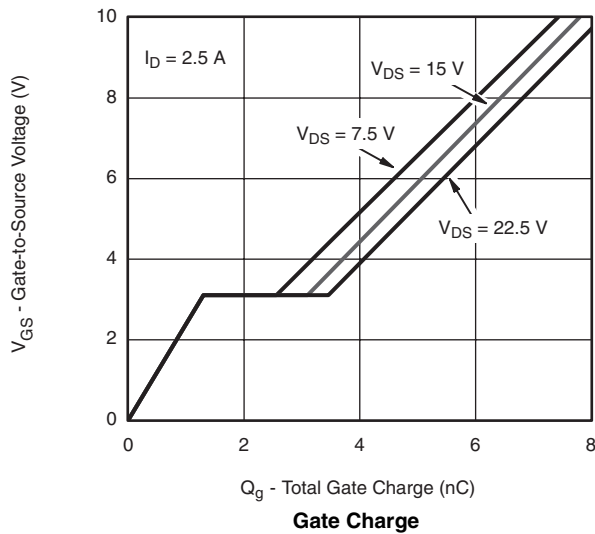
Transfer Characteristics



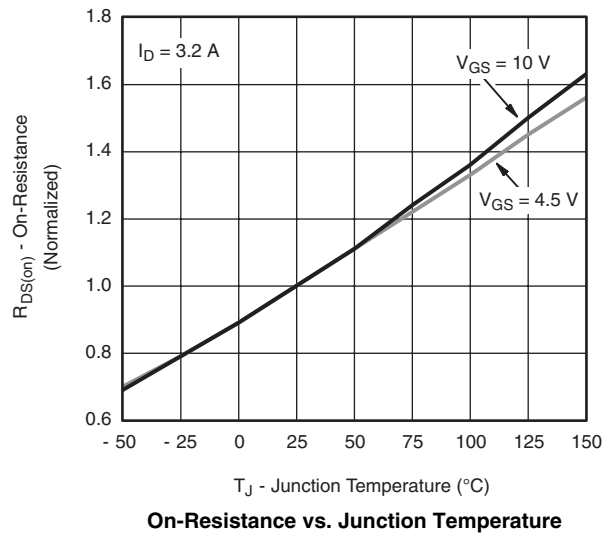
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



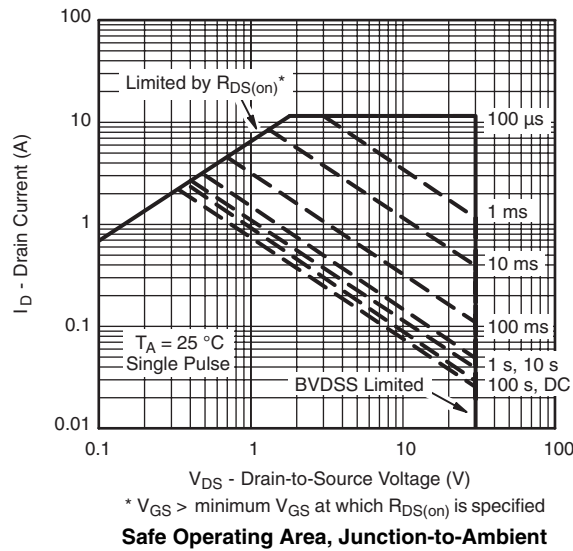
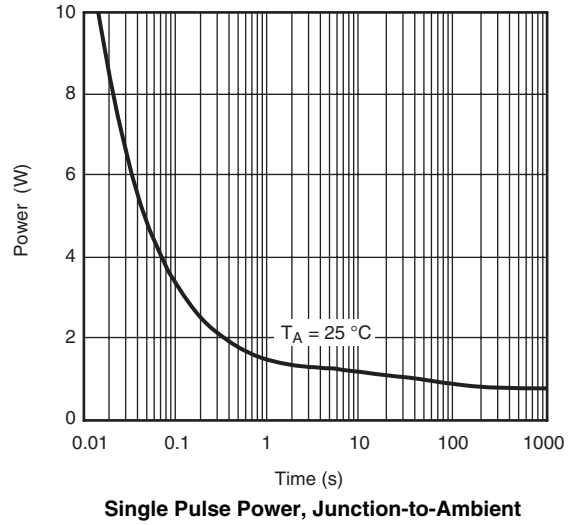
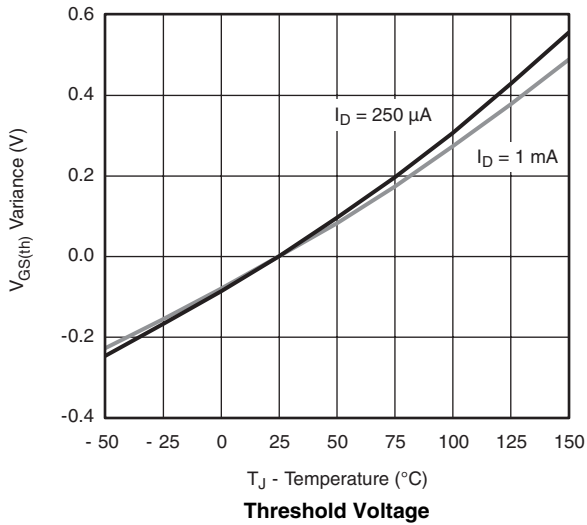
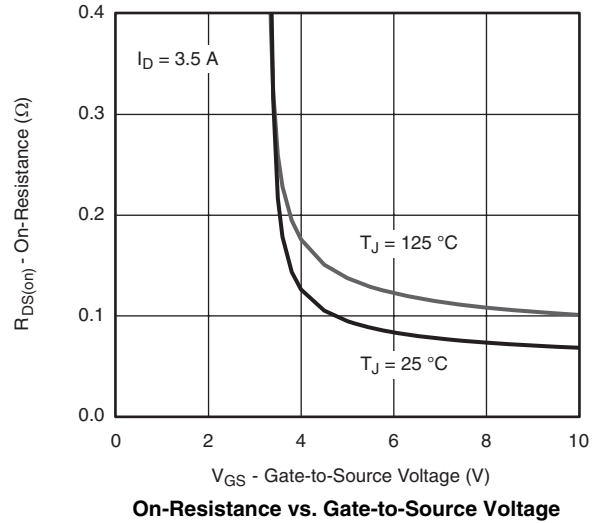
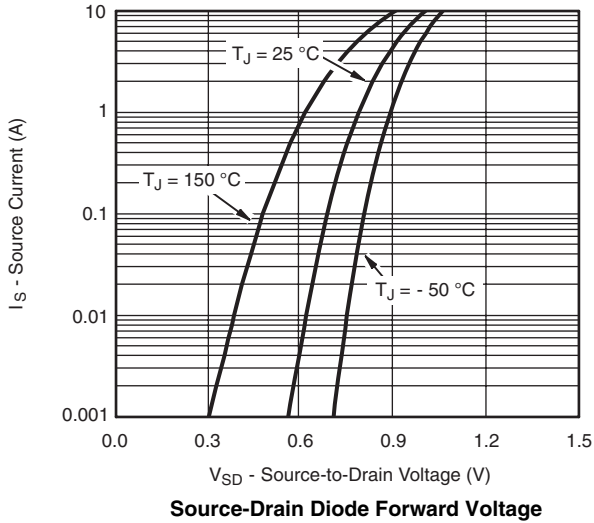
Gate Charge



On-Resistance vs. Junction Temperature

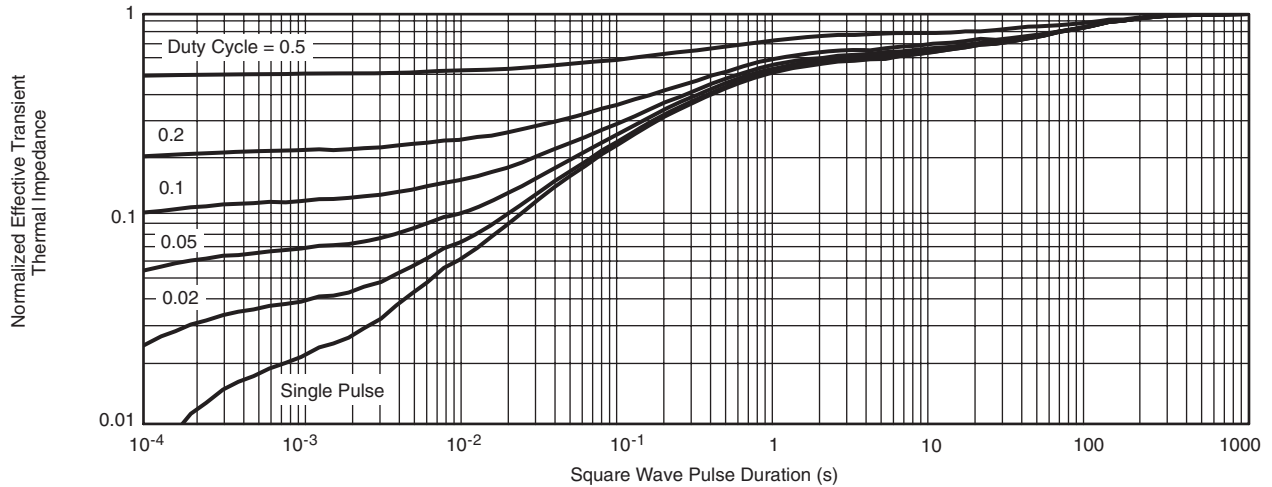


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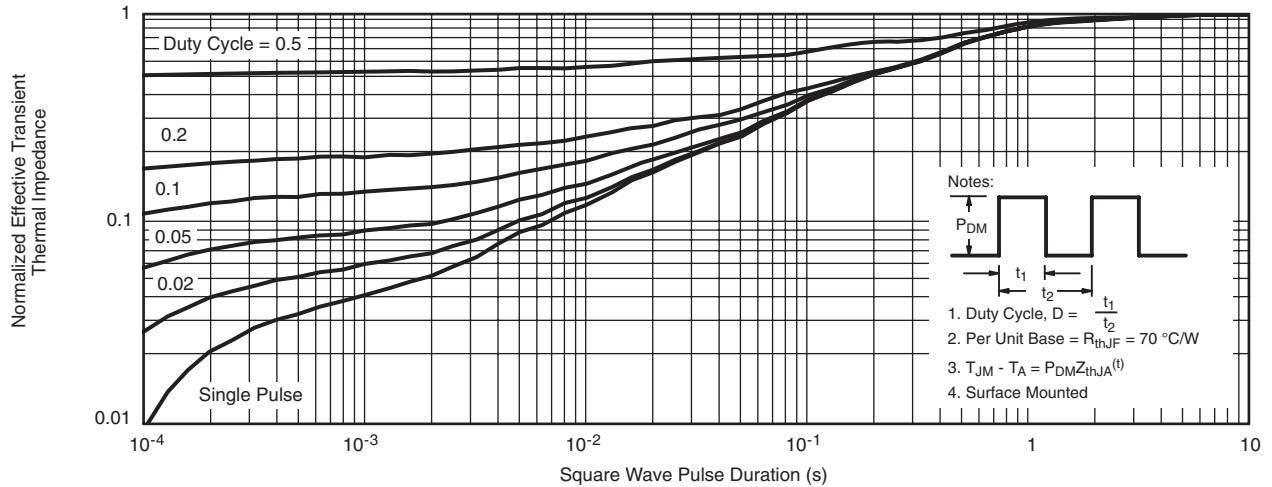




TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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